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Vishay Siliconix

Automotive N-Channel 60 V (D-S) 175 °C MOSFET

PowerPAK® 1212-8W Single D D 8 D D 8 D D 8 D D 8 D D 8 D D 8 S D D 7 S D D 7 S D D 7 S D D 7 S D D 8 D

Marking code: Q056

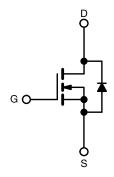
PRODUCT SUMMARY	
V _{DS} (V)	60
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0300
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.0410
I _D (A)	8
Configuration	Single
Package	PowerPAK 1212-8W

FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912







N-Channel MOSFET

ORDERING INFORMATION	
Package	PowerPAK 1212-8W
Lead (Pb)-free and halogen-free	SQS460CENW

ABSOLUTE MAXIMUM RATINGS (T	_C = 25 °C, unles	s otherwise noted)		
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-source voltage		V _{DS}	60		
Gate-source voltage		V _{GS}	± 20	V	
Continuous drain current a	T _C = 25 °C	1	8		
Continuous drain current "	T _C = 125 °C	l _D	8		
Continuous source current (diode conduction) a		I _S	8	Α	
Pulsed drain current b		I _{DM}	32		
Single pulse avalanche current	L = 0.1 mH	I _{AS}	13.5		
Single pulse avalanche energy	L = U.T IIII	E _{AS}	9.11	mJ	
Maximum nawar dissination	T _C = 25 °C	В	27	W	
Maximum power dissipation	T _C = 125 °C	P _D	9		
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +175	°C	
Soldering recommendations (peak temperature) d, e			260		

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount c	R _{thJA}	81	°C/W
Junction-to-case (drain)		R_{thJC}	5.5	C/VV

Notes

- a. Package limited
- b. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %
- c. When mounted on 1" square PCB (FR4 material)
- d. See solder profile (www.vishay.com/doc?73257). The PowerPAK1212-8W package may have visible exposed Cu at the end of the lead terminals due to the singulation process. However, the leads also have plated indents on the top and bottom surfaces that promote the formation of a solder filet compatible with automated optical inspection methods
- e. Rework conditions: manual soldering with a soldering iron is not recommended



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PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V _{DS}	V _{GS}	= 0, I _D = 250 μA	60	-	-	.,
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$		1.5	2.0	2.5	V
Gate-source leakage	I _{GSS}	V _{DS} =	0 V, V _{GS} = ± 20 V	-	-	± 100	nA
		$V_{GS} = 0 V$	V _{DS} = 60 V	-	-	1	
Zero gate voltage drain current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 60 V, T _J = 125 °C	=	-	50	μA
		V _{GS} = 0 V	V _{DS} = 60 V, T _J = 175 °C	-	-	150	
On-state drain current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	20	-	-	Α
		V _{GS} = 10 V	I _D = 5.3 A	-	0.0240	0.0300	
Duit and an allele social and a	Б	V _{GS} = 10 V	I _D = 5.3 A, T _J = 125 °C	-	-	0.0480	
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 5.3 A, T _J = 175 °C	-	-	0.0590	Ω
		V _{GS} = 4.5 V	I _D = 4 A	-	0.0330	0.0410	
Forward transconductance b	9 _{fs}	V _{DS} =	= 15 V, I _D = 5.3 A	-	19	-	S
Dynamic ^b		•					
Input capacitance	C _{iss}			-	493	580	
Output capacitance	C _{oss}	$V_{GS} = 0 V$	V _{DS} = 25 V, f = 1 MHz	-	226	290	pF
Reverse transfer capacitance	C _{rss}			-	13	20	
Total gate charge ^c	Qg			-	7.2	11	
Gate-source charge ^c	Q _{gs}	V _{GS} = 10 V	$V_{DS} = 30 \text{ V}, I_D = 4.5 \text{ A}$	-	2.15	-	nC
Gate-drain charge ^c	Q _{gd}			-	0.55	-	
Gate resistance	R _g	f = 1 MHz		0.63	1.27	1.90	Ω
Turn-on delay time ^c	t _{d(on)}			-	9	14	
Rise time ^c	t _r	V _{DD} =	= 30 V, $R_L = 30 \Omega$	-	3	5	ns
Turn-off delay time ^c	t _{d(off)}	$I_D \cong 1 \stackrel{\text{BB}}{A}, V$	$V_{\rm GEN} = 10 \rm V, R_g = 1 \Omega$	-	16	24	
Fall time ^c	t _f			-	15	23	
Source-Drain Diode Ratings and Charact	eristic ^b	,			•		
Pulsed current ^a	I _{SM}			-	-	32	А
Forward voltage	V _{SD}	I _F = 6 A, V _{GS} = 0 V		-	0.845	1.1	V
Body diode reverse recovery time	t _{rr}			-	15	30	ns
Body diode reverse recovery charge	Q _{rr}	- I _F = 5 A, di/dt = 100 A/μs		=	8	16	nC
Reverse recovery fall time	ta			-	9	-	
Reverse recovery rise time	t _b			-	6	-	ns
Body diode peak reverse recovery current	I _{RM(REC)}			_	-1	-	Α

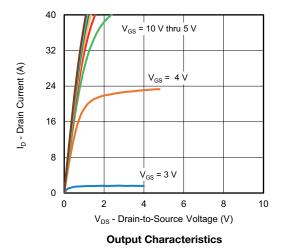
Notes

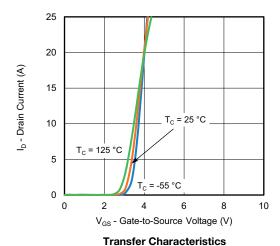
- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

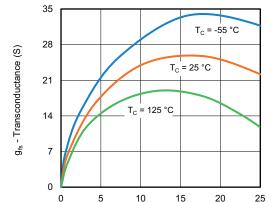
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

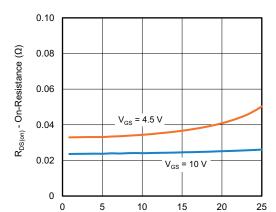


TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

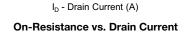


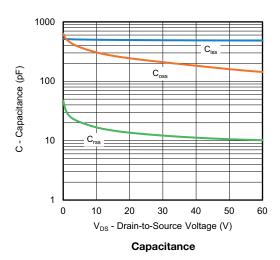


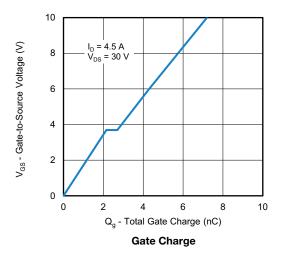




I_D - Drain Current (A) **Transconductance**

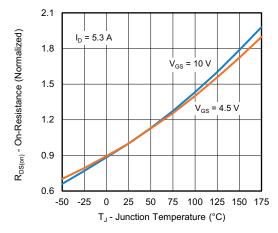




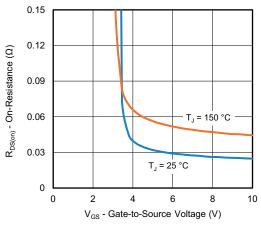




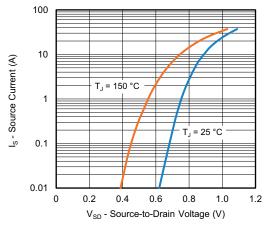
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



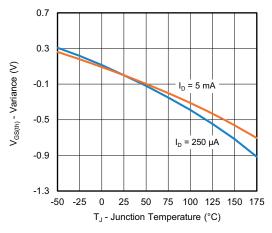
On-Resistance vs. Junction Temperature



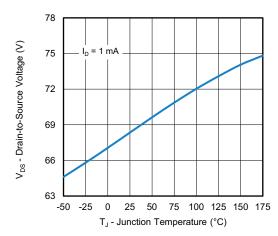
On-Resistance vs. Gate-to-Source Voltage



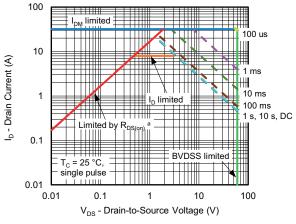
Source Drain Diode Forward Voltage



Threshold Voltage



Drain Source Breakdown vs. Junction Temperature



Safe Operating Area

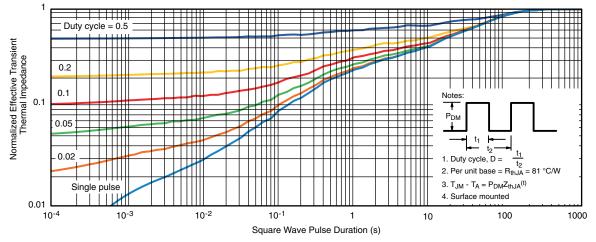
Note

a. V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

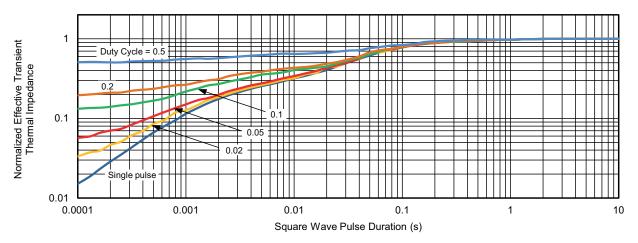
For technical questions, contact: automostech



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Note

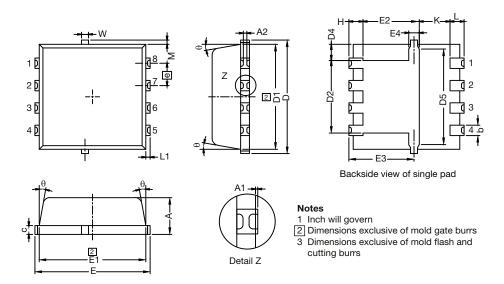
- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?63156.



PowerPAK® 1212-8W Case Outline



DIM.		MILLIMETERS			INCHES	
DIIVI.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
Α	0.97	1.04	1.12	0.038	0.041	0.044
A1	0	-	0.05	0	-	0.002
A2	0	-	0.13	0	-	0.005
b	0.23	0.30	0.41	0.009	0.012	0.016
С	0.23	0.28	0.33	0.009	0.011	0.013
D	3.20	3.30	3.40	0.126	0.130	0.134
D1	2.95	3.05	3.15	0.116	0.120	0.124
D2	1.98	2.11	2.24	0.078	0.083	0.088
D4	0.47 typ.			0.0185 typ.		
D5		2.3 typ.		0.090 typ.		
E	3.20	3.30	3.40	0.126	0.130	0.134
E1	2.95	3.05	3.15	0.116	0.120	0.124
E2	1.47	1.60	1.73	0.058	0.063	0.068
E3	1.75	1.85	1.98	0.069	0.073	0.078
E4		0.34 typ.		0.013 typ.		
е		0.65 BSC.		0.026 BSC		
K		0.86 typ.		0.034 typ.		
Н	0.30	0.41	0.51	0.012	0.016	0.020
L	0.30	0.43	0.56	0.012	0.017	0.022
L1	0.06	0.13	0.20	0.002	0.005	0.008
θ	0°	-	12°	0°	-	12°
W	0.15	0.25	0.36	0.006	0.010	0.014
М	0.125 typ.			0.125 typ. 0.005 typ.		

DWC: 6020

DWG: 6032



RECOMMENDED MINIMUM PADS FOR PowerPAK® 1212-8 Single



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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